

Abstract

Radiation-emitting semiconductor component

In a radiation-emitting semiconductor component with a layer structure (12) which includes a photon-emitting active layer (16), an n-doped cladding layer (14) and a p-doped cladding layer (18), a contact connected to the n-doped cladding layer (14) and a mirror layer (20) connected to the p-doped cladding layer (18), according to the invention the mirror layer (20) is formed by an alloy of silver comprising one or more metals selected from the group consisting of Ru, Rh, Pd, Au, Os, Ir, Pt, Cu, Ti, Ta and Cr.

Figure 1